

MUN2130, MMUN2130L, MUN5130, DTA113EE, DTA113EM3, NSBA113EF3

Digital Transistors (BRT) R1 = 1 kΩ, R2 = 1 kΩ

PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

| Rating | Symbol | Max | Unit |
|--------------------------------|----------------------|-----|------|
| Collector-Base Voltage | V _{CBO} | 50 | Vdc |
| Collector-Emitter Voltage | V _{CEO} | 50 | Vdc |
| Collector Current - Continuous | I _C | 100 | mAdc |
| Input Forward Voltage | V _{IN(fwd)} | 10 | Vdc |
| Input Reverse Voltage | V _{IN(rev)} | 10 | Vdc |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



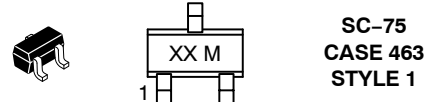
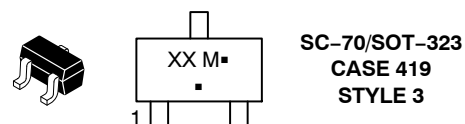
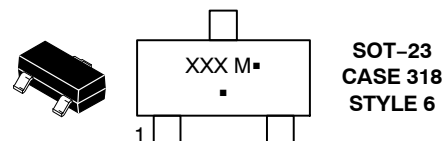
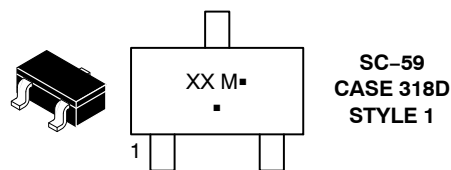
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PIN CONNECTIONS



MARKING DIAGRAMS



- XXX = Specific Device Code
- M = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

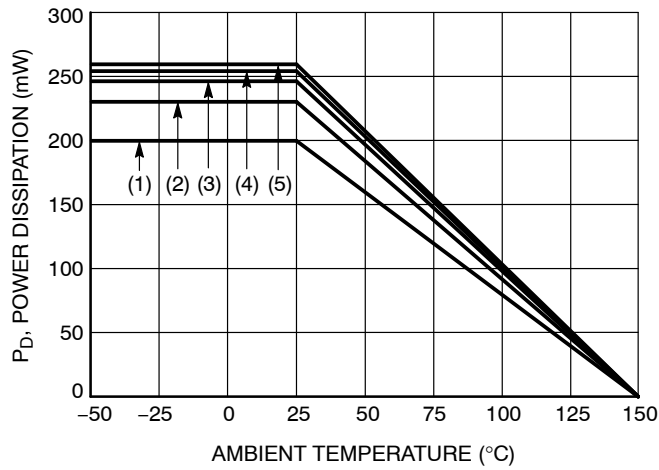
MUN2130, MMUN2130L, MUN5130, DTA113EE, DTA113EM3, NSBA113EF3

Table 1. ORDERING INFORMATION

| Device | Part Marking | Package | Shipping† |
|--------------------------------|--------------|----------------------------|--------------------|
| MUN2130T1G | 6G | SC-59 (Pb-Free) | 3000 / Tape & Reel |
| MMUN2130LT1G | A6G | SOT-23 (Pb-Free) | 3000 / Tape & Reel |
| MUN5130T1G | 6G | SC-70/SOT-323 (Pb-Free) | 3000 / Tape & Reel |
| DTA113EET1G | 6G | SC-75 (Pb-Free) | 3000 / Tape & Reel |
| DTA113EM3T5G, NSVDTA113EM3T5G* | 7E | SOT-723 (Pb-Free) | 8000 / Tape & Reel |
| NSBA113EF3T5G | L (180°)** | SOT-1123 (Pb-Free) | 8000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

** (xx°) = Degree rotation in the clockwise direction.



- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm², 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Figure 1. Derating Curve

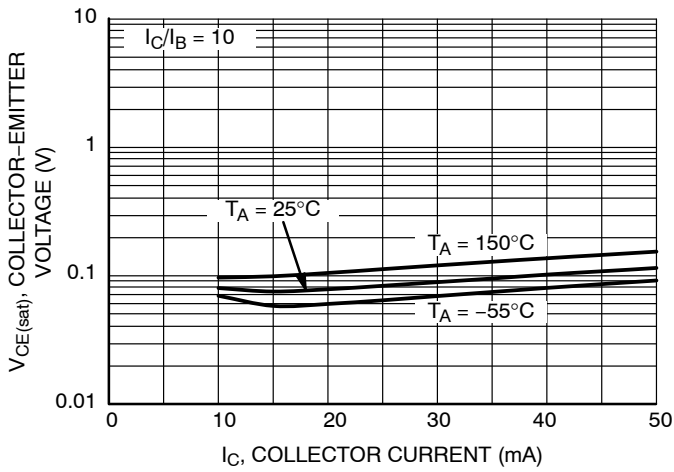


Figure 2. $V_{CE(sat)}$ vs. I_C

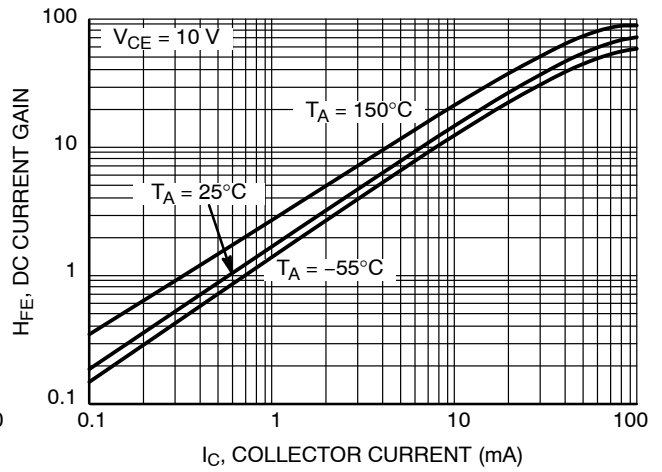


Figure 3. DC Current Gain

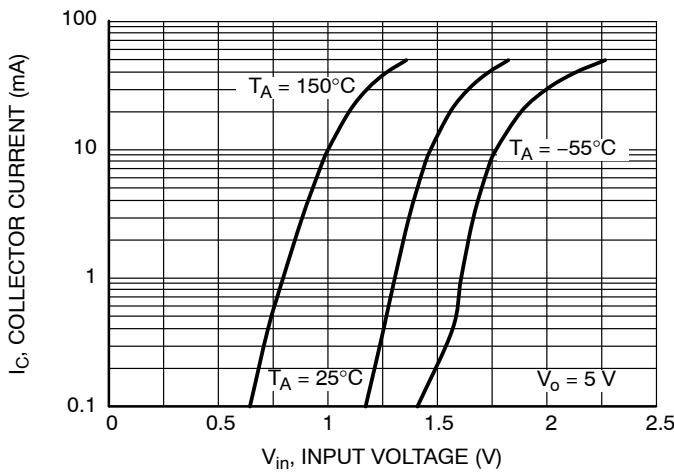


Figure 4. Output Current vs. Input Voltage

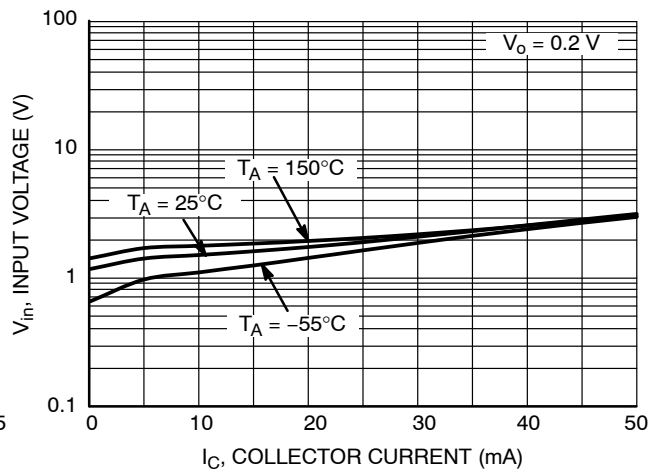


Figure 5. Input Voltage vs. Output Current

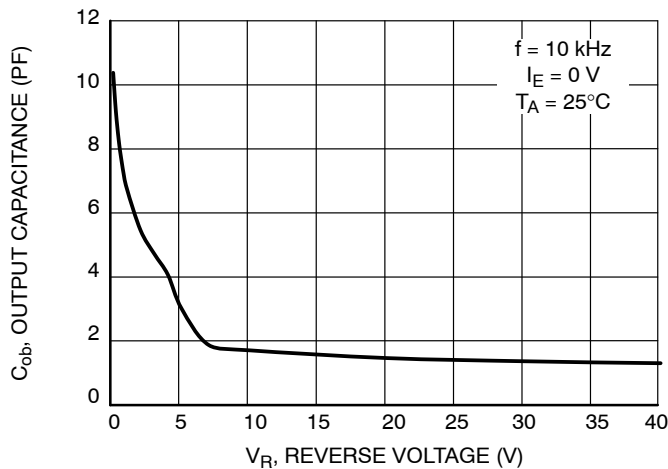


Figure 6. Output Capacitance

MUN2130, MMUN2130L, MUN5130, DTA113EE, DTA113EM3, NSBA113EF3

Table 2. THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|--|-----------------------------------|----------------------------|
| THERMAL CHARACTERISTICS (SC-59) (MUN2130) | | | |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C | (Note 1) (Note 2) (Note 1) (Note 2) | P_D 230 338 1.8 2.7 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{\theta JA}$ 540 370 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction to Lead | (Note 1) (Note 2) | $R_{\theta JL}$ 264 287 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |
| THERMAL CHARACTERISTICS (SOT-23) (MMUN2130L) | | | |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C | (Note 1) (Note 2) (Note 1) (Note 2) | P_D 246 400 2.0 3.2 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{\theta JA}$ 508 311 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction to Lead | (Note 1) (Note 2) | $R_{\theta JL}$ 174 208 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |
| THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5130) | | | |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C | (Note 1) (Note 2) (Note 1) (Note 2) | P_D 202 310 1.6 2.5 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{\theta JA}$ 618 403 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction to Lead | (Note 1) (Note 2) | $R_{\theta JL}$ 280 332 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |
| THERMAL CHARACTERISTICS (SC-75) (DTA113EE) | | | |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C | (Note 1) (Note 2) (Note 1) (Note 2) | P_D 200 300 1.6 2.4 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{\theta JA}$ 600 400 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |
| THERMAL CHARACTERISTICS (SOT-723) (DTA113EM3) | | | |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C | (Note 1) (Note 2) (Note 1) (Note 2) | P_D 260 600 2.0 4.8 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{\theta JA}$ 480 205 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
- FR-4 @ 500 mm², 1 oz. copper traces, still air.

MUN2130, MMUN2130L, MUN5130, DTA113EE, DTA113EM3, NSBA113EF3

Table 2. THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|-------------|---------------------------|
| THERMAL CHARACTERISTICS (SOT-1123) (NSBA113EF3) | | | |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ | P_D | 254 297 | mW |
| Derate above 25°C | | 2.0 2.4 | mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 493 421 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction to Lead | $R_{\theta JL}$ | 193 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
- FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|--|---------------|-----|-----|------|------------|
| OFF CHARACTERISTICS | | | | | |
| Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}, I_E = 0$) | I_{CBO} | - | - | 100 | nAdc |
| Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}, I_B = 0$) | I_{CEO} | - | - | 500 | nAdc |
| Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}, I_C = 0$) | I_{EBO} | - | - | 4.3 | mAdc |
| Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}, I_E = 0$) | $V_{(BR)CBO}$ | 50 | - | - | Vdc |
| Collector-Emitter Breakdown Voltage (Note 5) ($I_C = 2.0\text{ mA}, I_B = 0$) | $V_{(BR)CEO}$ | 50 | - | - | Vdc |
| ON CHARACTERISTICS | | | | | |
| DC Current Gain (Note 5) ($I_C = 5.0\text{ mA}, V_{CE} = 10\text{ V}$) | h_{FE} | 3.0 | 5.0 | - | |
| Collector-Emitter Saturation Voltage (Note 5) ($I_C = 10\text{ mA}, I_B = 5.0\text{ mA}$) | $V_{CE(sat)}$ | - | - | 0.25 | Vdc |
| Input Voltage (off) ($V_{CE} = 5.0\text{ V}, I_C = 100\ \mu\text{A}$) | $V_{i(off)}$ | - | 1.2 | 0.5 | Vdc |
| Input Voltage (on) ($V_{CE} = 0.3\text{ V}, I_C = 20\text{ mA}$) | $V_{i(on)}$ | 2.0 | 1.6 | - | Vdc |
| Output Voltage (on) ($V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 1.0\text{ k}\Omega$) | V_{OL} | - | - | 0.2 | Vdc |
| Output Voltage (off) ($V_{CC} = 5.0\text{ V}, V_B = 0.05\text{ V}, R_L = 1.0\text{ k}\Omega$) | V_{OH} | 4.9 | - | - | Vdc |
| Input Resistor | R_1 | 0.7 | 1.0 | 1.3 | k Ω |
| Resistor Ratio | R_1/R_2 | 0.8 | 1.0 | 1.2 | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulsed Condition: Pulse Width = 300 msec, Duty Cycle $\leq 2\%$.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS | | | INCHES | | |
|----------------|-------------|------|------|--------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| c | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| H _E | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| T | 0° | --- | 10° | 0° | --- | 10° |

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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| DESCRIPTION: | SOT-23 (TO-236) | PAGE 1 OF 2 |

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MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

- | | | | | | |
|---|---|---|---|---|---|
| STYLE 1 THRU 5: CANCELLED | STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE | | |
| STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE | STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE | STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE | STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE |
| STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE | STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE | STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE | STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE | STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE | STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE |
| STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN | STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT | STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE | STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE | STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION |
| STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE | STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE | | | | |

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| DESCRIPTION: | SOT-23 (TO-236) | PAGE 2 OF 2 |

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 4:1

SC-70 (SOT-323) CASE 419 ISSUE R

DATE 11 OCT 2022



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

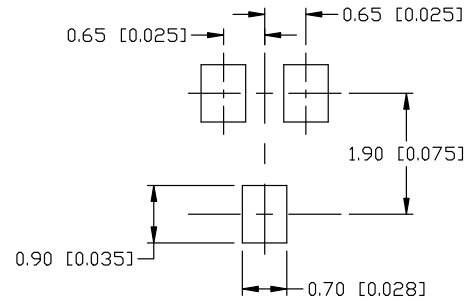
| DIM | MILLIMETERS | | | INCHES | | |
|----------------|-------------|------|------|-----------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 0.80 | 0.90 | 1.00 | 0.032 | 0.035 | 0.040 |
| A1 | 0.00 | 0.05 | 0.10 | 0.000 | 0.002 | 0.004 |
| A2 | 0.70 REF | | | 0.028 BSC | | |
| b | 0.30 | 0.35 | 0.40 | 0.012 | 0.014 | 0.016 |
| c | 0.10 | 0.18 | 0.25 | 0.004 | 0.007 | 0.010 |
| D | 1.80 | 2.00 | 2.20 | 0.071 | 0.080 | 0.087 |
| E | 1.15 | 1.24 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e1 | 0.65 BSC | | | 0.026 BSC | | |
| L | 0.20 | 0.38 | 0.56 | 0.008 | 0.015 | 0.022 |
| H _E | 2.00 | 2.10 | 2.40 | 0.079 | 0.083 | 0.095 |

GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

SOLDERING FOOTPRINT

- | | | | | | |
|---|---|---|--|---|---|
| STYLE 1: CANCELLED | STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE | STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE | |
| STYLE 6: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 7: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN | STYLE 9: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE | STYLE 10: PIN 1. CATHODE 2. ANODE 3. ANODE-CATHODE | STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE |

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| DESCRIPTION: | SC-70 (SOT-323) | PAGE 1 OF 1 |

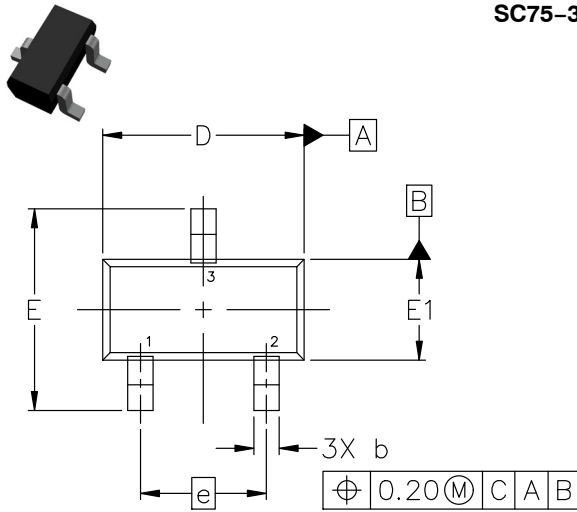
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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

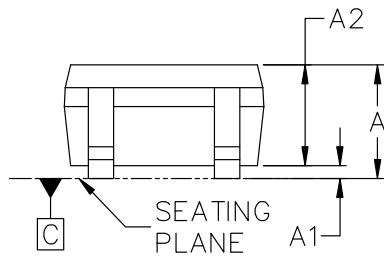


SC75-3 1.60x0.80x0.80, 1.00P
CASE 463
ISSUE H

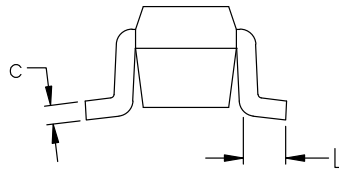
DATE 01 FEB 2024



TOP VIEW

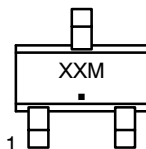


SIDE VIEW



END VIEW

GENERIC MARKING DIAGRAM*



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

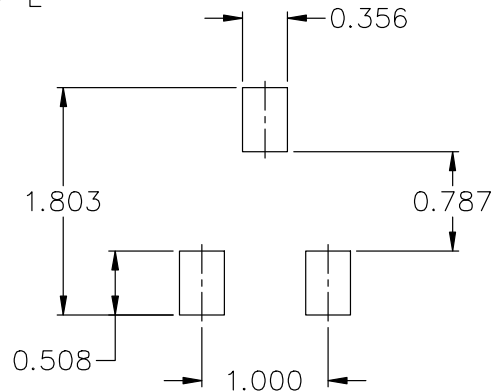
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
- STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE
- STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE
- STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE
- STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.70 | 0.80 | 0.90 |
| A1 | 0.00 | 0.05 | 0.10 |
| A2 | 0.80 REF. | | |
| b | 0.15 | 0.20 | 0.30 |
| c | 0.10 | 0.15 | 0.25 |
| D | 1.55 | 1.60 | 1.65 |
| E | 1.50 | 1.60 | 1.70 |
| E1 | 0.70 | 0.80 | 0.90 |
| e | 1.00 BSC | | |
| L | 0.10 | 0.15 | 0.20 |



RECOMMENDED MOUNTING FOOTPRINT*

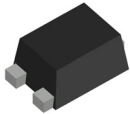
* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

| | | |
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| DESCRIPTION: | SC75-3 1.60x0.80x0.80, 1.00P | PAGE 1 OF 1 |

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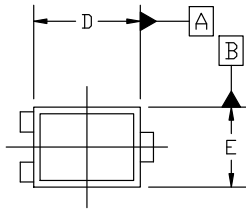
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

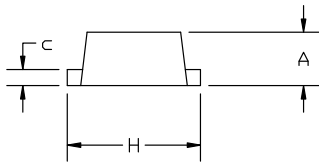


SOT-1123 0.80x0.60x0.37, 0.35P
CASE 524AA
ISSUE D

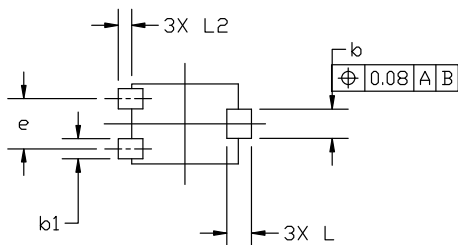
DATE 18 JAN 2024



TOP VIEW

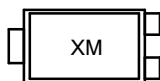


SIDE VIEW



BOTTOM VIEW

GENERIC MARKING DIAGRAM*



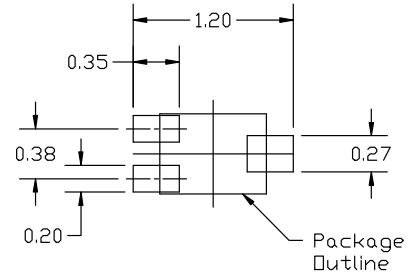
X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| MILLIMETERS | | | |
|-------------|-----------|-------|-------|
| DIM | MIN | NOM | MAX |
| A | 0.34 | 0.37 | 0.40 |
| b | 0.15 | 0.22 | 0.28 |
| b1 | 0.10 | 0.15 | 0.20 |
| c | 0.07 | 0.12 | 0.17 |
| D | 0.75 | 0.80 | 0.85 |
| E | 0.55 | 0.60 | 0.65 |
| e | 0.35 | 0.38 | 0.40 |
| H | 0.950 | 1.000 | 1.050 |
| L | 0.185 REF | | |
| L2 | 0.05 | 0.10 | 0.15 |



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERM/D.

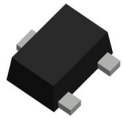
| | | | | |
|---|--|--|--|--|
| STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE | STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN |
|---|--|--|--|--|

| | | |
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| DESCRIPTION: | SOT-1123 0.80x0.60x0.37, 0.35P | PAGE 1 OF 1 |

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



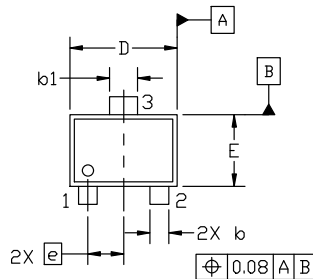
SOT-723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E

DATE 24 JAN 2024

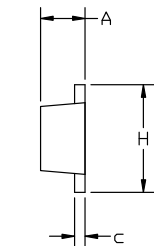
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

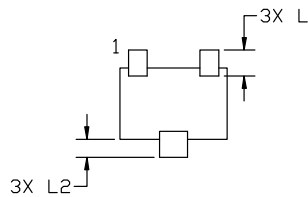
| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.45 | 0.50 | 0.55 |
| b | 0.15 | 0.21 | 0.27 |
| b1 | 0.25 | 0.31 | 0.37 |
| c | 0.07 | 0.12 | 0.17 |
| D | 1.15 | 1.20 | 1.25 |
| E | 0.75 | 0.80 | 0.85 |
| e | 0.40 BSC | | |
| H | 1.15 | 1.20 | 1.25 |
| L | 0.29 REF | | |
| L2 | 0.15 | 0.20 | 0.25 |



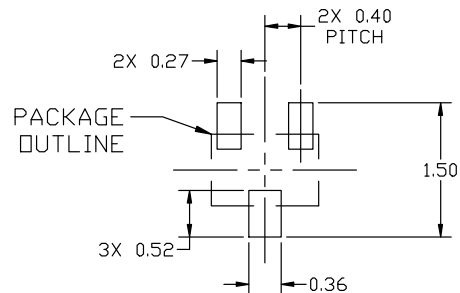
TOP VIEW



SIDE VIEW

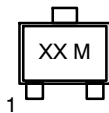


BOTTOM VIEW



RECOMMENDED MOUNTING FOOTPRINT

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| STYLE 1: | STYLE 2: | STYLE 3: | STYLE 4: | STYLE 5: |
|--------------|--------------|--------------|----------------|-------------|
| PIN 1. BASE | PIN 1. ANODE | PIN 1. ANODE | PIN 1. CATHODE | PIN 1. GATE |
| 2. EMITTER | 2. N/C | 2. ANODE | 2. CATHODE | 2. SOURCE |
| 3. COLLECTOR | 3. CATHODE | 3. CATHODE | 3. ANODE | 3. DRAIN |

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